Jong-Won Lim

List of Publications by Year
in descending order

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33	137	1307594 7	1199594 12
papers	citations	h-index	g-index

33	33	33	172
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	X-Band GaN Monolithic Microwave Integrated Circuit Low Noise Amplifier Using Inductive Source Degeneration. The Journal of Korean Institute of Electromagnetic Engineering and Science, 2022, 33, 356-364.	0.3	0
2	Analysis of Parasitic Effects by Bonding Structure. , 2021, , .		0
3	Thermal Behavior of an AlGaN/GaN-Based Schottky Barrier Diode on Diamond and Silicon Substrates. Journal of Nanoscience and Nanotechnology, 2021, 21, 4429-4433.	0.9	0
4	Switching and heat-dissipation performance analysis of an LTCC-based leadless surface mount package using a power factor correction converter. , 2021, , .		0
5	Power module stray inductance extraction: Theoretical and experimental analysis. ETRI Journal, 2021, 43, 891-899.	2.0	1
6	Substrate Effects on the Electrical Properties in GaN-Based High Electron Mobility Transistors. Crystals, 2021, 11, 1414.	2.2	4
7	Van der Waals Heterostructure of Hexagonal Boron Nitride with an AlGaN/GaN Epitaxial Wafer for High-Performance Radio Frequency Applications. ACS Applied Materials & Interfaces, 2021, 13, 59440-59449.	8.0	8
8	Stability and reliability of LTCC-based 5/12Ââ€‹V dual output DC-DC converter with high efficiency and small size. Microelectronics Journal, 2020, 106, 104937.	2.0	6
9	Charging Effect by Fluorine-Treatment and Recess Gate for Enhancement-Mode on AlGaN/GaN High Electron Mobility Transistors. Nanomaterials, 2020, 10, 2116.	4.1	3
10	Comprehensive Research of Total Ionizing Dose Effects in GaN-Based MIS-HEMTs Using Extremely Thin Gate Dielectric Layer. Nanomaterials, 2020, 10, 2175.	4.1	8
11	Recess-Etched and Tetramethylammonium Hydroxide-Treated Nanoscale Pattern on AlGaN/GaN High-Electron-Mobility-Transistors for Improved Ohmic Contact. Journal of the Korean Physical Society, 2020, 76, 837-842.	0.7	0
12	Thermal Analysis and Operational Characteristics of an AlGaN/GaN High Electron Mobility Transistor with Copper-Filled Structures: A Simulation Study. Micromachines, 2020, 11, 53.	2.9	16
13	Multi-layer ceramic based surface mount device packaging for 1200 V and 1700 V SiC SBD power semiconductors. , 2020, , .		0
14	Efficiency improvement of power conversion system with multilayer power inductor. , 2020, , .		1
15	DC Characteristics of AlGaN/GaN High-Electron Mobility Transistor with a Bottom Plate Connected to Source-Bridged Field Plate Structure. Journal of Nanoscience and Nanotechnology, 2019, 19, 2319-2322.	0.9	5
16	77âˆ¼97 GHz LNA MMIC with 1 dB-Gain Flatness Using Short-Circuited Capacitor. , 2019, , .		0
17	Improvement of Proton Radiation Hardness Using ALD-Deposited Al₂O₃ÂGate Insulator in GaN-Based MIS-HEMTs. ECS Journal of Solid State Science and Technology, 2019, 8, Q245-Q248.	1.8	9
18	Total-Ionizing-Dose Responses of GaN-Based HEMTs With Different Channel Thicknesses and MOSHEMTs With Epitaxial MgCaO as Gate Dielectric. IEEE Transactions on Nuclear Science, 2018, 65, 46-52.	2.0	12

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19	High Figure-of-Merit (${V}_{ext{BR}}^{ext{2}}$ /${R}_{ext{ON}}$) AlGaN/GaN Power HEMT With Periodically C-Doped GaN Buffer and AlGaN Back Barrier. IEEE Journal of the Electron Devices Society, 2018, 6, 1179-1186.	2.1	29
20	Operational Improvement of AlGaN/GaN High Electron Mobility Transistor by an Inner Field-Plate Structure. Applied Sciences (Switzerland), 2018, 8, 974.	2.5	20
21	Growth of 10 nmâ€thick AlIn(Ga)N/GaN heterostructure with high electron mobility and low sheet resistance. Physica Status Solidi (B): Basic Research, 2017, 254, 1600731.	1.5	2
22	Characteristics of enhanced-mode AlGaN/GaN MIS HEMTs for millimeter wave applications. Journal of the Korean Physical Society, 2017, 71, 365-369.	0.7	7
23	Design of a low temperature co-fired ceramics (LTCC) based antenna with broadband and high gain at 60GHz bands. , 2016, , .		0
24	Fabrication and electrical properties of an AlGaN/GaN HEMT on SiC with a taper-shaped backside via hole. Journal of the Korean Physical Society, 2015, 67, 718-722.	0.7	0
25	Ohmic contact to AlGaN/GaN heterostructures on sapphire substrates. Journal of the Korean Physical Society, 2015, 66, 779-784.	0.7	3
26	Analysis of the degradation of AlGaN/GaN HEMTs by high-temperature operation tests. Journal of the Korean Physical Society, 2014, 64, 1446-1450.	0.7	1
27	Characteristics of a 60 GHz MMIC mixer with an open stub microstrip line. Microwave and Optical Technology Letters, 2010, 52, 1341-1345.	1.4	1
28	Fabrication of AlGaN/GaN HEMT with the improved ohmic contact by encapsulation of silicon dioxide thin film. , 2010, , .		1
29	Fabrication of AlGaN/GaN HEMT with the improved ohmic contact by encapsulation of silicon dioxide thin film. , 2010, , .		0
30	Influence of Gate Head Dimensions on the Device performance of 0.12um PHEMT. , 2007, , .		0
31	Fabrication of SiN-assisted 0.12um AlGaAs/InGaAs PHEMT and 60GHz-band MMICs for 60GHz WPAN system. Materials Research Society Symposia Proceedings, 2006, 969, 1.	0.1	0
32	A 3 V GaAs MESFET monolithic transmitter with cross-coupled common-source, common-gate pair linear mixer for cellular hand-held phones. , 0, , .		0
33	A 3 V GaAs MESFET monolithic transmitter with cross-coupled common-source, common-gate pair linear mixer for cellular hand-held phones. , 0, , .		0